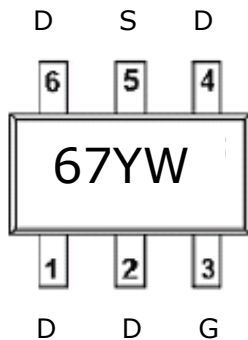


DESCRIPTION

The STP3467 is the P-Channel enhancement mode power field effect transistor which is produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application, such as cellular phone and notebook computer power management and other battery powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

PIN CONFIGURATION TSOP-6P

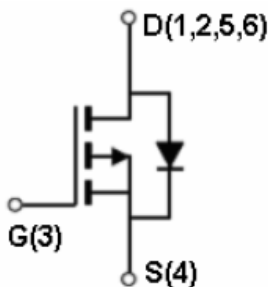


Y: Year

A: Week Code

FEATURE

- ◆ -20V/-5.0A, $R_{DS(ON)}=90\text{mohm}@V_{GS}=-4.5\text{V}$
- ◆ -20V/-3.5A, $R_{DS(ON)}=110\text{mohm}@V_{GS}=-2.5\text{V}$
- ◆ -20V/-1.7A, $R_{DS(ON)}=140\text{mohm}@V_{GS}=-1.8\text{V}$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional an-resistance and maximum DC current capability
- ◆ TSOP-6P package design



ORDERING INFORMATION

Part Number	Package	Part Marking
STP3467ST6RG	TSOP-6	67YW

※ Week Code Code : A ~ Z ; a ~ z

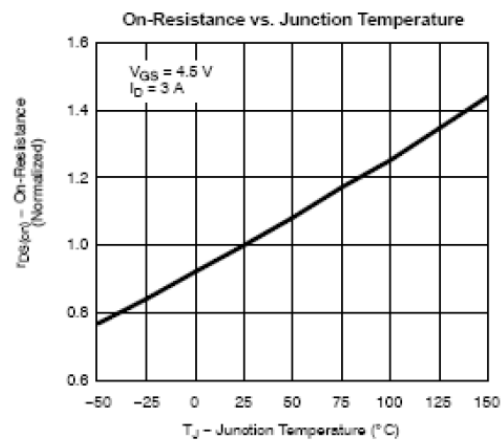
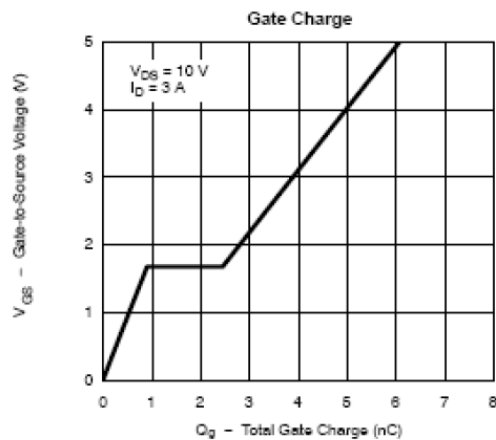
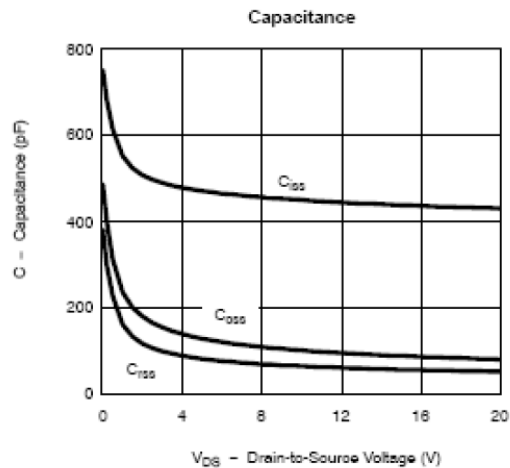
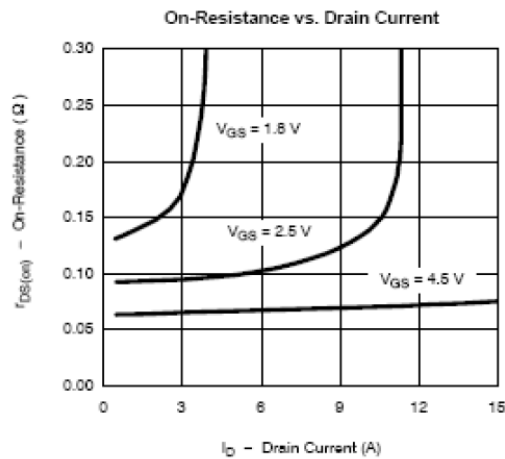
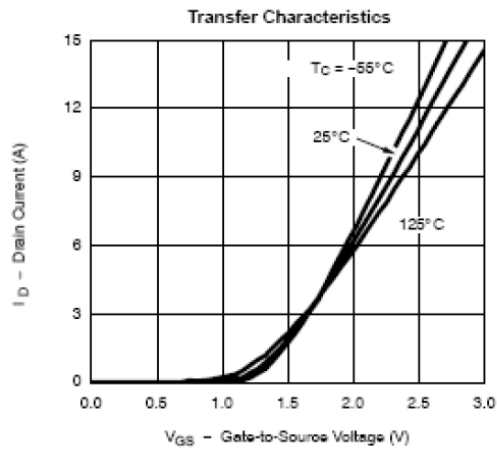
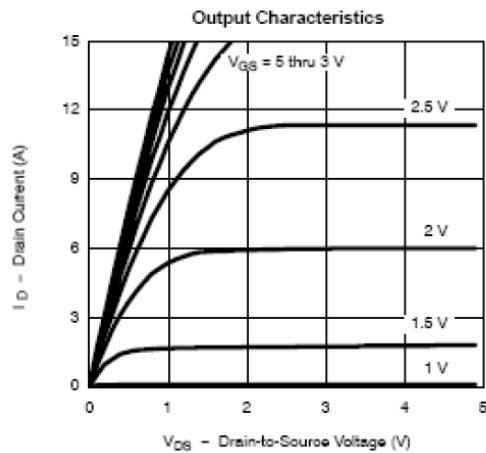
※ STP3467ST6RG ST6 : TSOP-6; R: Tape Reel ; G: Pb – Free

**STP3467**P Channel Enhancement Mode MOSFET
-5.2A**ABSOLUTE MAXIMUM RATINGS** (Ta = 25°C unless otherwise noted)

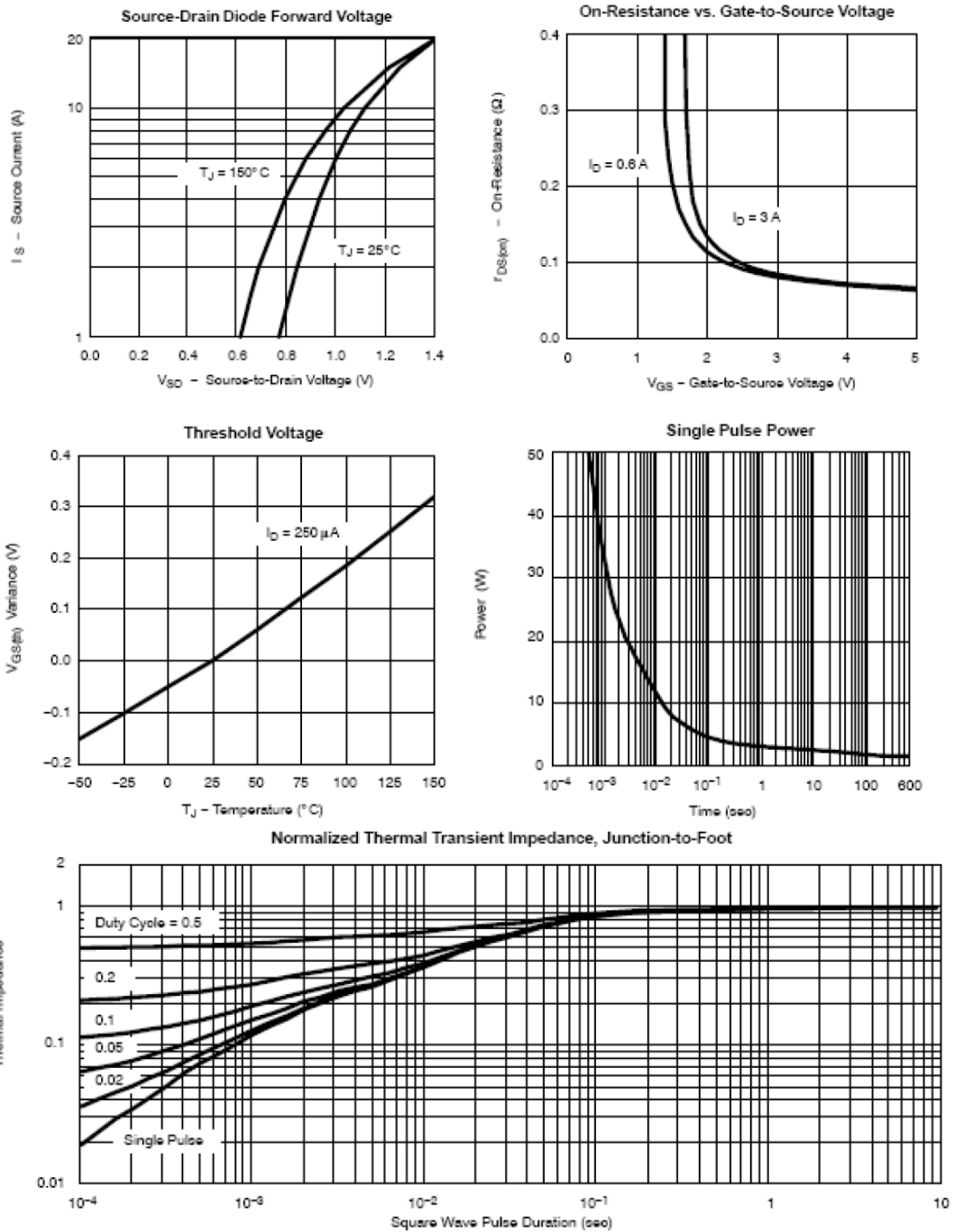
Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±12	V
Continuous Drain Current (T _J =150°C)	I _D	-5.2	A
T _A =25°C		-4.2	
T _A =70°C			
Pulsed Drain Current	I _{DM}	-20	A
Continuous Source Current (Diode Conduction)	I _S	-1.7	A
Power Dissipation	P _D	2.0	W
T _A =25°C		1.3	
T _A =70°C			
Operation Junction Temperature	T _J	-55/150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	90	°C/W

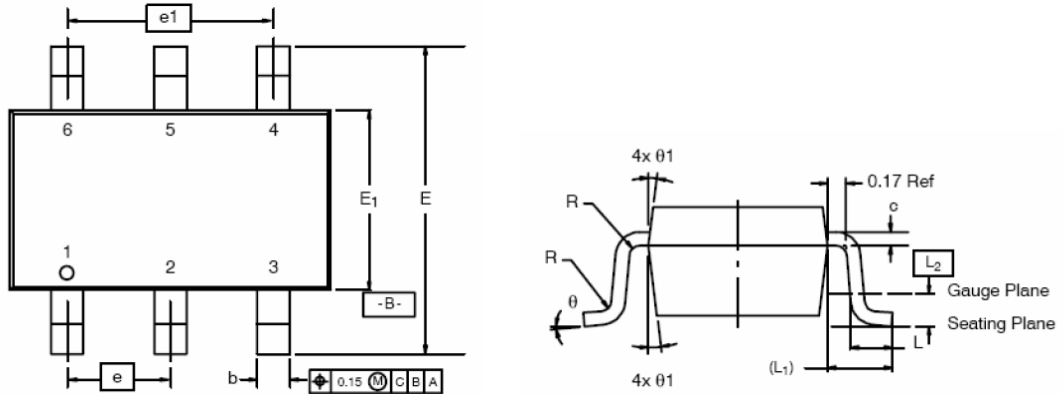
ELECTRICAL CHARACTERISTICS (Ta = 25°C Unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.35		-0.8	V
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$			-1	uA
		$V_{DS}=-20V, V_{GS}=0V$ $T_J=55^\circ C$			-5	
On-State Drain Current	$I_{D(on)}$	$V_{DS}\leq -5V, V_{GS}=-10V$	-6			A
Drain-source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-5.2A$		0.075	0.090	Ω
		$V_{GS}=-4.5V, I_D=-4.2A$		0.090	0.110	
		$V_{GS}=-1.8V, I_D=-1.7A$		0.120	0.140	
Forward Transconductance	g_{fs}	$V_{DS}=-5.0V, I_D=-2.8A$		-10		S
Diode Forward Voltage	V_{SD}	$I_S=-1.5A, V_{GS}=0V$		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=-6V, V_{GS}=-4.5V,$ $V_{DS}=-2.8A$		4.8	8	nC
Gate-Source Charge	Q_{gs}			1.0		
Gate-Drain Charge	Q_{gd}			1.0		
Input Capacitance	C_{iss}	$V_{DS}=-6V, V_{GS}=0,$ $f=1MHz$		485		pF
Output Capacitance	C_{oss}			85		
Reverse Transfer Capacitance	C_{rss}			40		
Turn-On Time	$T_{d(on)}$	$V_{DD}=-6V,$ $R_L=6\Omega, V_{GEN}=-4.5V$ $R_G=6\Omega$		10	15	ns
	t_r			15	25	
Turn-Off Time	$T_{d(off)}$			18	25	
	t_f			15	20	

TYPICAL CHARACTERISTICS


TYPICAL CHARACTERISTICS



TSOP-6 PACKAGE OUTLINE


Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
e	1.00 BSC			0.0394 BSC		
e ₁	1.90	2.00	2.10	0.075	0.080	0.085
L	0.35	-	0.50	0.014	-	0.020
L ₁	0.60 Ref			0.024 Ref		
L ₂	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ_1	7° Nom			7° Nom		